Preface

The 15th International Conference on Silicon Carbide and Related Materials (ICSCRM2013) was held in Miyazaki, Japan, from September 29 through October 4, 2013. The conference provided a scientific forum on the wide bandgap semiconductors for 794 participants from 24 countries.

The conference involved 361 papers including 27 invited presentations. The papers cover most of the current research efforts on the wide bandgap semiconductor silicon carbide (SiC) and related materials, and a wide range of topics from crystal growth to their power electronics applications. In these proceedings, the written version of 270 contributed papers and 13 invited papers are included. The major chapters of the proceedings collect papers in the area of bulk growth of SiC, epitaxial growth of SiC, physical properties and characterization, processing, devices and application. There are three shorter chapters on graphene, III-nitrides and related materials. We wish to thank all of the invited speakers for their outstanding presentation, and also thank all the contributors and participants.

The success of ICSCRM2013 is based on the hard work of many peoples behind the main scene. The International Steering committee and Advisory committee made many valuable suggestions regarding scientific and technical portion of the conference. The Technical Program committee members worked hard to organize the attractive technical program in two parallel oral sessions, and four poster sessions. A number of reviewers contribute greatly to maintain the high scientific standards of this publication. Also the success of the conference is due to the hard work of the members of the Executive including Local Arrangements and Sponsor Committees.

ICSCRM2013 is held in cooperation with 6 academic societies in Japan and financially supported by eight foundations including Miyazaki prefecture, and about 25 companies. We would like to take this opportunity to thank them again for their sponsorship and support.

Needless to say, preservation of the natural environment and prevention of global warming are one of the most serious issues in the 21st century. To solve these issue, saving and efficient usage of electric energy are essential. Most recently, power semiconductor technology using wide-bandgap semiconductor materials, typically represented by SiC, has been expected to play a very important role for that purpose. From now on, ICSCRM will be attracting attention more and more from many kinds of technical and social fields.

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The next conference of this series, ICSCRM2015, will be held in Giardini Naxos, Italy, from October 4 to 9, 2015 (http://icscrm2015.imm.cnr.it). The conference will be co-chaired by Fabrizio Roccaforte (CNR-IMM) and Francesco La Via (CNR-IMM). We wish the organizers much success.

January, 2014

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